Vishay Siliconix

Automotive P-Channel 12 V (D-S) 175 °C MOSFET



Marking Code: Q4005

PRODUCT SUMMARY				
V _{DS} (V)	-12			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.016			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 \text{ V}$	0.022			
I _D (A)	-15			
Configuration	Single			

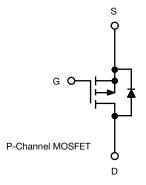
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified d
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and halogen-free	SQ4005EY (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-12	V	
Gate-source voltage		V _{GS}	± 8	V	
Continuous drain current ^a	T _C = 25 °C	1-	-15		
	T _C = 125 °C	- I _D	-8.7		
Continuous source current (diode conduction) ^a		I _S	-5.4	Α	
Pulsed drain current ^b		I _{DM}	-60		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-20		
Single pulse avalanche energy	L = 0.1 MH	E _{AS}	20	mJ	
Maximum power dissipation ^b	T _C = 25 °C	P _D	6	W	
	T _C = 125 °C	r _D	2	VV	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature)			260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB Mount c	R_{thJA}	92	°C/W
Junction-to-foot (drain)			25	C/VV

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0$, $I_D = -250 \mu A$		-12	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		-0.6	-1	
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	$V_{DS} = -12 \text{ V}$	-	-	-1	μΑ
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -12 V, T _J = 125 °C	-	-	-50	
		V _{GS} = 0 V	V _{DS} = -12 V, T _J = 175 °C	-	-	-150	
On-state drain current a	I _{D(on)}	V _{GS} = -4.5 V	$V_{DS} \le -5 \text{ V}$	-20	-	-	Α
		V _{GS} = -4.5 V	I _D = -13.5 A	-	0.013	0.016	
Drain aguras an atata registance 3	В	V _{GS} = -4.5 V	I _D = -13.5 A	-	-	0.020	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = -4.5 V	I _D = -13.5 A	-	-	0.022	Ω
		V _{GS} = -2.5 V	I _D = -12 A	-	0.018	0.022	
Forward transconductance b	9fs	V _{DS} = -6 V, I _D = -12 A		-	34	-	S
Dynamic ^b							
Input capacitance	C _{iss}		V _{GS} = 0 V V _{DS} = -6 V, f = 1 MHz	-	2433	3600	pF
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	922	1380	
Reverse transfer capacitance	C _{rss}			-	752	1120	
Total gate charge ^c	Qg			-	29	38	
Gate-source charge ^c	Q _{gs}	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -6 \text{ V}, I_{D} = -10 \text{ A}$	-	4.2	-	nC
Gate-drain charge c	Q_{gd}			-	8.4		
Gate resistance	Rg		f = 1 MHz		2.7	4	Ω
Turn-on delay time ^c	t _{d(on)}			-	19	26	
Rise time ^c	t _r	$V_{DD} = -6 \text{ V, } R_L = 0.6 \Omega$ $I_D \cong -10 \text{ A, } V_{GEN} = -4.5 \text{ V, } R_g = 1 \Omega$		-	33	44	ns
Turn-off delay time ^c	t _{d(off)}			-	73	97	
Fall time ^c	t _f			-	30	40	
Source-Drain Diode Ratings and Char	acteristics b						
Pulsed current ^a	I _{SM}				-	-60	Α
Forward voltage	V _{SD}	I _F = -10 A, V _{GS} = 0 V			-0.8	-1.1	V

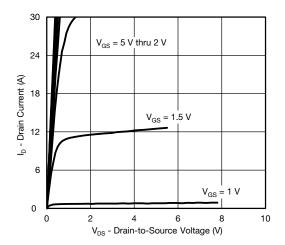
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

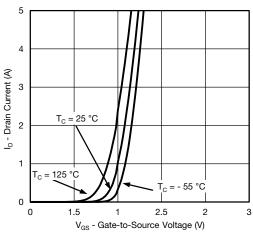
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



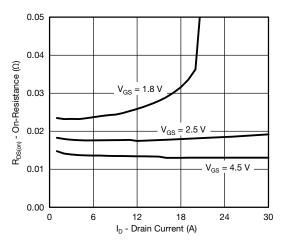
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



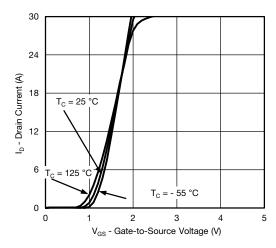
Output Characteristics



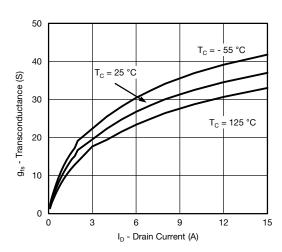
Transfer Characteristics



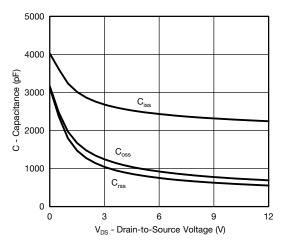
On-Resistance vs. Drain Current



Transfer Characteristics



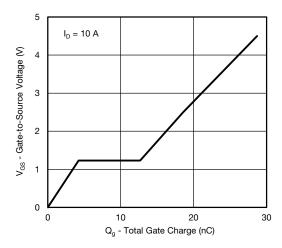
Transconductance



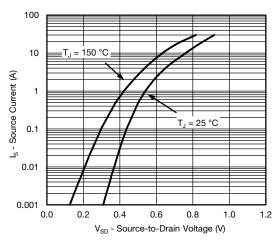
Capacitance



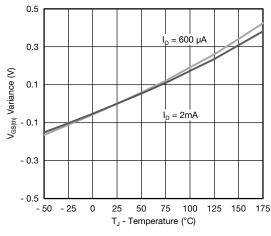
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



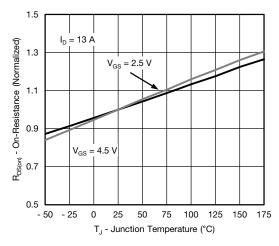
Gate Charge



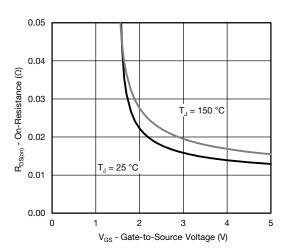
Source Drain Diode Forward Voltage



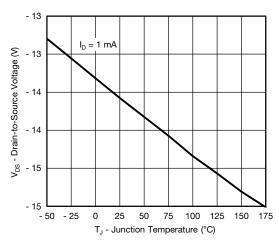
Threshold Voltage



On-Resistance vs. Junction Temperature

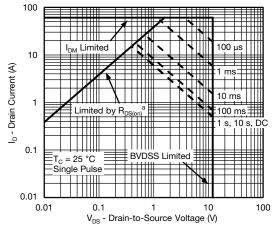


On-Resistance vs. Gate-to-Source Voltage



Breakdown Voltage vs. Junction Temperature

THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



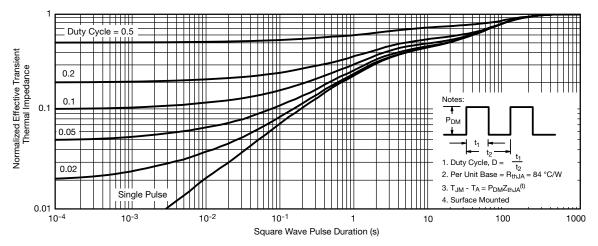
Safe Operating Area

Note

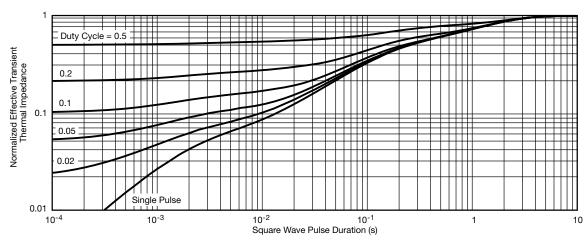
a. $V_{GS} > minimum \ V_{GS}$ at which $R_{DS(on)}$ is specified



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	INCHES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27 BSC		0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

DWG: 5498

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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